Songang Peng

List of Publications by Year in descending order

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1040056 1281871 11 139 9 11 citations h-index g-index papers 11 11 11 164 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	The Effect of Metal Contact Doping on the Scaled Graphene Field Effect Transistor. Advanced Engineering Materials, 2022, 24, 2100935.	3.5	12
2	Emerging Internet of Things driven carbon nanotubes-based devices. Nano Research, 2022, 15, 4613-4637.	10.4	23
3	Electric-Field Induced Doping Polarity Conversion in Top-Gated Transistor Based on Chemical Vapor Deposition of Graphene. Crystals, 2022, 12, 184.	2.2	10
4	Stable p-type chemical doping of graphene with reduced contact resistance by single-layer perfluorinated polymeric sulfonic acid. Nanotechnology, 2021, 32, 155705.	2.6	1
5	Role of hydrogen and oxygen in the study of substrate surface impurities and defects in the chemical vapor deposition of graphene. Carbon, 2021, 185, 82-95.	10.3	10
6	Controllable pâ€toâ€n Type Conductance Transition in Topâ€Cated Graphene Field Effect Transistor by Interface Trap Engineering. Advanced Electronic Materials, 2020, 6, 2000496.	5.1	25
7	A composite with a gradient distribution of graphene and its anisotropic electromagnetic reflection. RSC Advances, 2020, 10, 3314-3318.	3.6	3
8	Metalâ€Contactâ€Induced Transition of Electrical Transport in Monolayer MoS ₂ : From Thermally Activated to Variableâ€Range Hopping. Advanced Electronic Materials, 2019, 5, 1900042.	5.1	14
9	Growth promotion of vertical graphene on SiO ₂ /Si by Ar plasma process in plasma-enhanced chemical vapor deposition. RSC Advances, 2018, 8, 18757-18761.	3.6	12
10	Effects of carbon-based impurities on graphene growth. Physical Chemistry Chemical Physics, 2018, 20, 15419-15423.	2.8	11
11	Evidence of electric field-tunable tunneling probability in graphene and metal contact. Nanoscale, 2017, 9, 9520-9528.	5.6	18